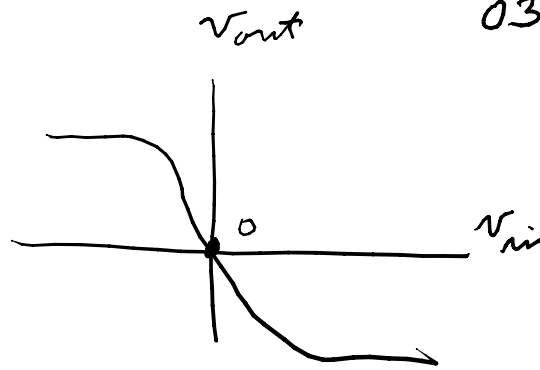
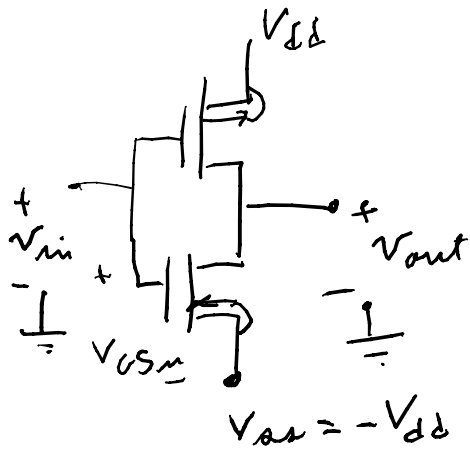


EE 302
03/08/05



$v_{in} = v_{out} = 0$ at transition

$$V_{GS_m} = v_{in} - V_{SS} = v_{in} + V_{DD}$$

$$V_{DS_m} = v_{out} - V_{SS} = v_{out} + V_{DD}$$

$$V_{GS_m} - V_{TO_m} = 0 + V_{DD} - V_{TO_m} < V_{DS_m} = 0 + V_{DD}$$

\Rightarrow NMOS is in saturation

$$I_{D_n} = \frac{K_P}{2} n \left(\frac{W}{L}\right)_m (V_{GS_m} - V_{TO_m})^2 (1 + \lambda_n V_{DS_m})$$

$$= \beta_m (V_{DD} - V_{TO_m})^2 (1 + \lambda_n V_{DD}); \text{ at transition midpoint}$$

$$\beta_m = \frac{K_P}{2} n \left(\frac{W}{L}\right)_m$$

PMOS also in saturation

$$V_{SG} = V_{DD} - v_{in} \quad V_{SD} = V_{DD} - v_{out}$$

$$-I_{D_p} = \beta_p (V_{DD} - |V_{TO_p}|)^2 (1 + \lambda_p V_{DD})$$

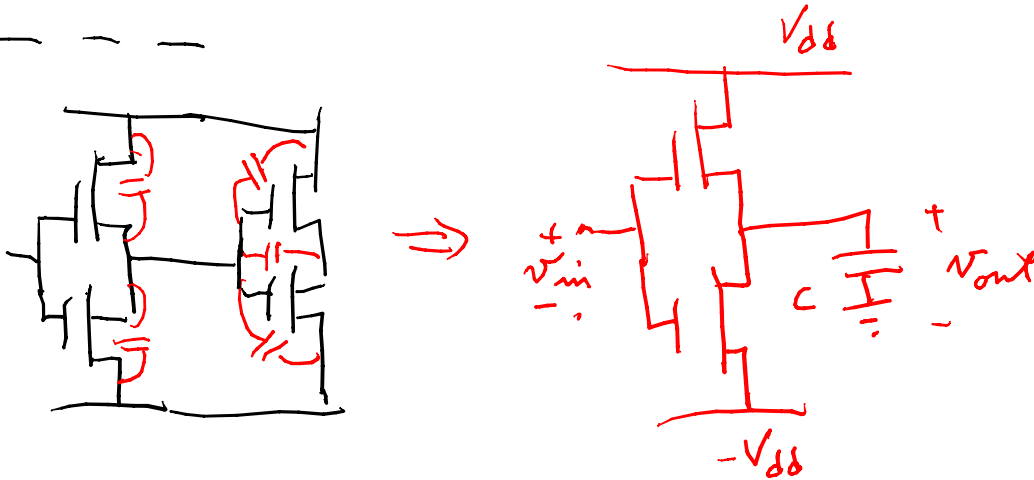
KCL: $I_{D_n} = -I_{D_p}$ gives an equation to design the inverter to transition at $v_{in} = 0$

$$\beta_n (V_{dd} - V_{TOn})^2 (1 + \lambda_n V_{DD}) = \beta_p (V_{dd} - |V_{TOp}|)^2 (1 + \lambda_p V_{dd})$$

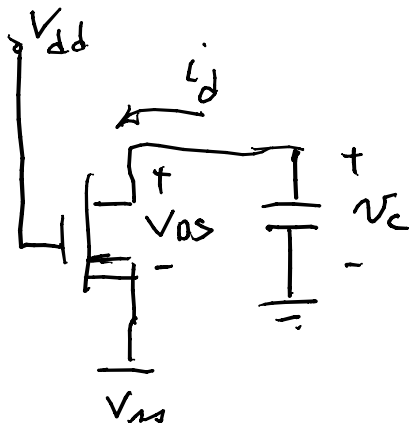
$$\beta_p = \beta_n \left(\frac{V_{dd} - V_{TOn}}{V_{dd} - |V_{TOp}|} \right)^2 \left(\frac{1 + \lambda_n V_{dd}}{1 + \lambda_p V_{dd}} \right)$$

if fix $\left(\frac{W}{L}\right)_n$ then this will give $\left(\frac{W}{L}\right)_p$

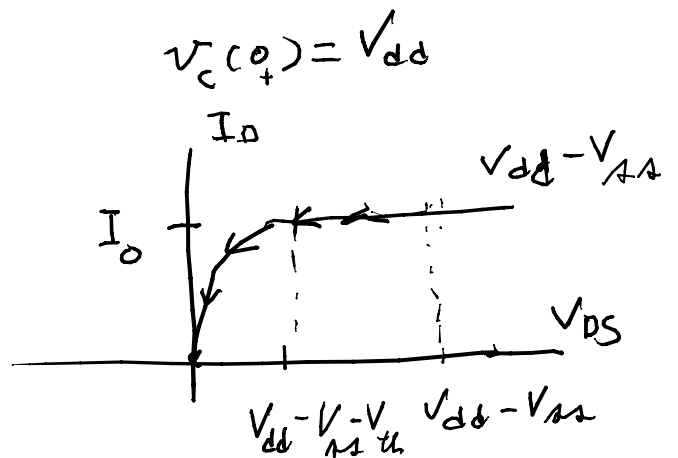
$$\left(\frac{W}{L}\right)_p = \left(\frac{K_{Pn}}{K_{Pp}}\right) \cdot \left(\frac{W}{L}\right)_n \left(\left(\frac{V_{dd} - V_{TOn}}{V_{dd} - |V_{TOp}|} \right)^2 \left(\frac{1 + \lambda_n V_{dd}}{1 + \lambda_p V_{dd}} \right) \right)$$



at $t=0$



i_d flows until drops to 0



stay in saturation as long as $V_{DS_m} > V_{dd} - V_{ds} - V_{TO_m}$

$$V_{DS_m} = v_c - V_{ds} \quad \text{"} \quad v_c - V_{ds}$$

that is as long as $v_c > V_{dd} - V_{th}$

$$\begin{aligned} \text{here } i_{D_m} &= \beta (V_{GS} - V_{TO_m})^2 (1 + \lambda V_{DS}) \\ &= \beta (V_{DD} - V_{th} - V_{TO_m})^2 (1 + \lambda [v_c - V_{ds}]) \end{aligned}$$

$$C \frac{dv_c}{dt} = -i_{D_m} = -\beta (2V_{dd} - V_{TO_m})^2 (1 + \lambda v_c + \lambda V_{dd})$$

while in saturation as long as $v_c > V_{dd} - V_{TO_m}$

to get time to do this

$$\frac{-C}{\beta (2V_{dd} - V_{TO_m})^2} \cdot \frac{dv_c}{(1 + \lambda V_{dd} + \lambda v_c)} = 1 dt$$

$$\frac{-C}{\beta (2V_{dd} - V_{TO_m})^2} \int_{V_{dd}}^{V_{dd} - V_{TO_m}} \frac{dv_c}{((1 + \lambda V_{dd}) + \lambda v_c)} = \int_0^{t_{SS}} dt$$

$$t_{SS} = \frac{C}{\beta (2V_{dd} - V_{TO_m})^2} \frac{1}{1 + \lambda V_{dd}} \cdot \int_{V_{dd} - V_{TO_m}}^{V_{dd}} \frac{dx = v_c}{\left(1 + \frac{\lambda}{1 + \lambda V_{dd}} x\right)}$$

time to get to ohmic

$$\frac{d(\ln(1 + ax))}{dx} = \frac{1}{1 + ax} \times a$$

$$\frac{1 + \lambda V_{dd}}{\lambda} \cdot \ln\left(1 + \frac{\lambda}{1 + \lambda V_{dd}} x\right) \Bigg|_{x = V_{dd} - V_{th}}^{V_{dd}}$$

gives

$$t_{SA} = \frac{C}{\beta(2V_{DD} - V_{TO_n})^2} \cdot \frac{1}{1 + \lambda V_{DD}} \times \frac{1 + \lambda V_{DD}}{\lambda} \cdot \ln \left(\frac{1 + \frac{\lambda}{1 + \lambda V_{DD}} V_{DD}}{1 + \frac{\lambda}{1 + \lambda V_{DD}} (V_{DD} - V_{th})} \right)$$

Eq. 4.152: $\frac{C V_{th}}{\beta(2V_{DD} - V_{TO_n})^2}$ which is the above as $\lambda \rightarrow 0$

at this time $v_C = V_{DD} - V_{TO_n}$

Now the transistor becomes ohmic

$$i_{d_n} = \beta(2(V_{GS} - V_{TO_n})V_{DS} - V_{DS}^2); \quad \begin{aligned} V_{DS} &= v_C - V_{DD} \\ &= v_C + V_{DD} \end{aligned}$$

$$= -C \frac{dv_C}{dt} = \beta(2(2V_{DD} - V_{TO_n})(v_C + V_{DD}) - (v_C + V_{DD})^2)$$

$$\frac{dv_C}{dt} = -\frac{\beta}{C} \left[V_{DD}(2(2V_{DD} - V_{TO_n}) - V_{DD}) + (2V_{DD} - 2V_{TO_n})v_C - v_C^2 \right]$$

$$dt = \frac{C}{\beta} \cdot \frac{dv_C}{v_C^2 - 2(V_{DD} - V_{TO_n})v_C - V_{DD}(2(2V_{DD} - V_{TO_n}) - V_{DD})}$$

$$t_2 = \frac{C}{\beta} \int_{V_{DD} - V_{TO_n}}^0 \frac{dv_C}{v_C^2 - (a)v_C - (b)}$$

" 0 in book (4.154)
as $V_{DD} = 0$

gives the time to fully discharge the capacitor.

(will keep "discharging" [charges in opposite direction] until hit $v_{SA} = -V_{DD}$)

$t_2 + t_{SA}$ = Time to change the state of the next gate
note as $C \downarrow$ this time decreases

